

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ASMEX.186DV1APPLICATION NO.
UnknownINFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Raaijmakers et al.FILING DATE
HerewithGROUP
UnknownJc976 U.S. PTO
09/764,711
01/18/01

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
AM	3,900,597	08/19/75	Chruma et al.			
	4,062,707	12/13/77	Mochizuki et al.			
	4,217,374	08/12/80	Ovshinsky et al.			
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	4,341,818	07/27/82	Adams et al.			
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	4,444,812	04/24/84	Gutsche			
	4,466,922	08/21/84	Weitz et al.			
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	5,198,387	3/99	Tang			
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						YES	NO
AK	51-1389 ✓	1976	Japan			Yes	
AK	54-4066 ✓	1979	Japan			Yes	
AK	60-36662 ✓	1985	Japan			Yes	
AK	63-3414 ✓	1986	Japan			Yes	
AK	63-239811 ✓		Japan			Yes	
AK	63-258016 ✓		Japan				
AK	2-119223 ✓	1990	Japan				
AK	2-122076 ✓	1990	Japan			Yes	
AK	2-208293 ✓		Japan			Yes	

EXAMINER
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OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

AK	✓ Bloem, J. "High Chemical Vapour Deposition Rates of Epitaxial Silicon Layers", J. of Crystal Growth, Vol. 18, 1973, pp. 70-76. ✓
	✓ Bunshah et al. "Deposition Technologies for Films and Coatings; Developments and Applications," Noyes Publications, 1982, p. 357. ✓
	✓ Claasen et al., "The Deposition Of Silicon From Silane In a Low-Pressure Hot-Wall System", J. of Crystal Growth, Vol. 57, 1982, pp. 259-266. ✓
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	✓ C.R. Kleijn, "A Mathematical Model of the Hydrodynamics and Gas-Phase Reactions in Silicon LPCVD in a Single-Wafer Reactor," J. Electrochem Soc., Vol 138, No. 7, July 1991, pp. 1190-1200.

EXAMINER

DATE CONSIDERED

12/3/01

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.